

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Akira Takahashi

Group Art Unit: Unknown

Divisional of Serial No. 10/259,351

Examiner: Unknown

Filed: February 18, 2004

For: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING SAME

INFORMATION DISCLOSURE STATEMENT
(SUBMISSION WITH CONTINUATION-IN-PART OR
RULE 1.53(b) CONTINUATION OR DIVISIONAL APPLICATION)

U.S. Patent and Trademark Office
2011 South Clark Place
Customer Window, **Mail Stop Patent Application**
Crystal Plaza Two, Lobby, Room 1B03
Arlington, VA 22202

Date: February 18, 2004

Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, Applicant hereby submits an Information Disclosure Statement for consideration by the Examiner.

I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications or other information submitted for consideration by the Office are listed on PTO-1449 form(s), attached hereto.

II. REFERENCES PREVIOUSLY CITED OR SUBMITTED

Pursuant to 37 C.F.R. § 1.98(d), consideration of information listed on the PTO-1449 form(s) is requested since any patents, publications or other information which are listed on the PTO-1449 form(s) but for which copies are not enclosed herewith, were previously cited by or submitted to the PTO in one of the following applications which has been relied upon for an earlier filing date under 35 U.S.C. § 120:

U.S. Serial Number10/259,351
09/713,025U.S. Filing DateSeptember 30, 2002
November 16, 2000III. FEES

This Information Disclosure Statement is being filed concurrent with the filing of a continuation-in-part, continuation or divisional patent application; therefore, no fee is required.

If the Examiner has any questions concerning this IDS or requires a copy of any of the references cited but not provided, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 50-0238.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 50-0238 for any additional fee required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

VOLENTINE FRANCOS, P.L.L.C.



Andrew J. Telesz, Jr.
Reg. No. 33,581

12200 Sunrise Valley Drive, Suite 150
Reston, VA 20191
Tel. No. (703) 715-0870
Fax No. (703) 715-0877

Enclosure: Two (2) PTO-1449 Forms

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) OIP.024D2		Application Number NEW		
				Applicant(s) Akira Takahashi				
				Filing Date February 18, 2004		Group Art Unit Unknown		
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	A	5,899,721	5/1999	Gardner et al.				
	B	6,245,625	6/2001	Gau				
	C	6,495,889	12/2002	Takahashi				
	D	5,610,092	3/1997	Tasaka				
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
	E	10-4190	1/06/1998	Japan				
	F	2000-49340	2/18/2000	Japan				
	G	9-45908	2/14/1997	Japan				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
	H	Tomohisa Mizuno et al., "Hot-Carrier Injection Suppression Due to the Nitride-Oxide LDD Spacer Structure," IEEE Transactions on Electron Devices, Vol. 38, No. 3, March 1991, pages 548-591.						
	I	F.C. Hsu et al., "Structure-Enhanced MOSFET Degradation Due to Hot-Electron Injection," IEEE Electron Device Letters, Vol. EDL-5, No. 3, March 1984, pages 71-74.						
EXAMINER				DATE CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)
OIP.024D

Application Number
NEW

Applicant(s)
Akira Takahashi

Filing Date
February 18, 2004

Group Art Unit
Unknown

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	J	Ahn et al., "Hot-Carrier degradation of single-drain PMOSFET's with differing sidewall spacer thicknesses", IEEE electron device letters, Vol. 13, 04/1992, pp. 711-713.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.